

Title (en)
HIGH SILICON STAINLESS

Title (de)
SILICIUMREICHER NICHTTROTENDER STAHL

Title (fr)
ACIER INOXYDABLE A TENEUR ELEVEE EN SILICIUM

Publication
EP 1352980 A4 20041117 (EN)

Application
EP 00981731 A 20001214

Priority
JP 0008877 W 20001214

Abstract (en)
[origin: EP1352980A1] A high-Si stainless steel excellent in various characteristics, inclusive of strength, corrosion resistance, workability and castability, consists of, on the mass % basis, Si: 2 to 5%, Cr: 8 to 25%, Ni: 4 to 16%, Mn: not more than 5%, Cu: not more than 4%, Co: not more than 8%, Mo: not more than 4%, Nb: not more than 3%, Ta: not more than 3%, Ti: not more than 3%, W: not more than 4%, V: not more than 4%, B: not more than 0.01%, Mg: not more than 0.01%, Ca: not more than 0.01%, rare earth elements: not more than 0.01%, the balance being Fe. Impurities in this steel are as follows: C: not more than 0.04%, P: not more than 0.03%, S: not more than 0.02%, Al: not more than 0.03%, N (nitrogen): not more than 0.05%, O (oxygen): not more than 0.005%, and H (hydrogen): not more than 0.0003%. <IMAGE>

IPC 1-7
C22C 38/00; **C22C 38/40**; **C22C 38/58**; **C22C 38/34**; **C22C 38/42**; **C22C 38/44**; **C22C 38/48**; **C22C 38/50**; **C22C 38/52**

IPC 8 full level
C22C 38/04 (2006.01); **C22C 38/34** (2006.01); **C22C 38/42** (2006.01); **C22C 38/44** (2006.01); **C22C 38/48** (2006.01); **C22C 38/50** (2006.01); **C22C 38/52** (2006.01); **C22C 38/58** (2006.01)

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• [A] PATENT ABSTRACTS OF JAPAN vol. 1998, no. 01 30 January 1998 (1998-01-30)
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